

TBD



Examination Cover Sheet

COURSE: ELEC	NUMBER: 311	SECTION(S): 2/F	
EXAMINATION: <input checked="" type="checkbox"/> FINAL <input type="checkbox"/> ALTERNATE <input type="checkbox"/> DEFERRED VERSION: _____	DATE: December 11, 2015	TIME: 14:00-17:00 Exam Length: 3 hours	PAGES: 5 including cover
INSTRUCTOR(S): Dr. R. Raut		DIVISION:	
MATERIALS ALLOWED: <input checked="" type="checkbox"/> Booklets <input type="checkbox"/> IBM (Scantron) <input type="checkbox"/> Blue <input type="checkbox"/> Green <input type="checkbox"/> Printed Translation Dictionary Other _____ <input checked="" type="checkbox"/> Calculator <input checked="" type="checkbox"/> ENCS Approved <input type="checkbox"/> Other _____		INSTRUCTIONS: <input checked="" type="checkbox"/> Return all <input type="checkbox"/> Answer on Exam <input type="checkbox"/> Open book <input type="checkbox"/> Crib sheet Details _____	

SPECIAL INSTRUCTIONS:

You are required to answer SIX questions

You MUST attempt Q.1 : 10 marks

From Q.2-Q.7, answer any FIVE questions.: 10 marks (each)

Before submitting your answer book, fill in the Table below indicating the answers you want to be graded.

(If you do not fill in the Table, the instructor will mark your answers as they appear one after another in the answer book)

Table

Answers to be graded	Q.1 (compulsory)					
Marks						

Show all steps clearly in neat and legible handwriting.

(Some important formulae)

$I_C = \beta I_B, I_E = (\beta + 1)I_B$	$g_m = \frac{I_C}{V_T}, r_\pi = \frac{\beta}{g_m}, \alpha = \frac{\beta}{\beta + 1}$	$r_o = \frac{V_A}{I_C}, r_e = \frac{r_\pi}{\beta + 1},$ $I_C = I_S \exp(V_{BE}/V_T)$
$I_D = k \left(\frac{W}{L} \right) \left((V_{GS} - V_t) V_{DS} - \frac{V_{DS}^2}{2} \right)$ (linear region)	$I_D = k \left(\frac{W}{2L} \right) (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$ (saturation region)	$g_m = k \left(\frac{W}{L} \right) (V_{GS} - V_{TH}) = \sqrt{\frac{2kI_D W}{L}}$ $r_o = \frac{V_A}{I_D}$

Part I: The student MUST answer this question (10 marks)

Q.1: A semiconductor junction diode **D** is used in an automatic gain control system as shown in figure 1. The ac resistance of the diode is dependent on the amplitude V_p of the input signal. The capacitance acts as a *short circuit* and the inductor acts as an *open circuit* for the ac signal.

The input signal is full-wave rectified to generate a DC voltage which drives the DC current through the diode. This DC voltage is given by $2V_p / \pi$. The diode is a 1 mA diode. For the diode you may use the relation: $V_2 = V_1 + 2.303nV_T \log_{10}(I_2 / I_1)$, where V_T is the thermal voltage ($=25$ mV). You may use $n = 1$. The DC resistance of the diode can be neglected.

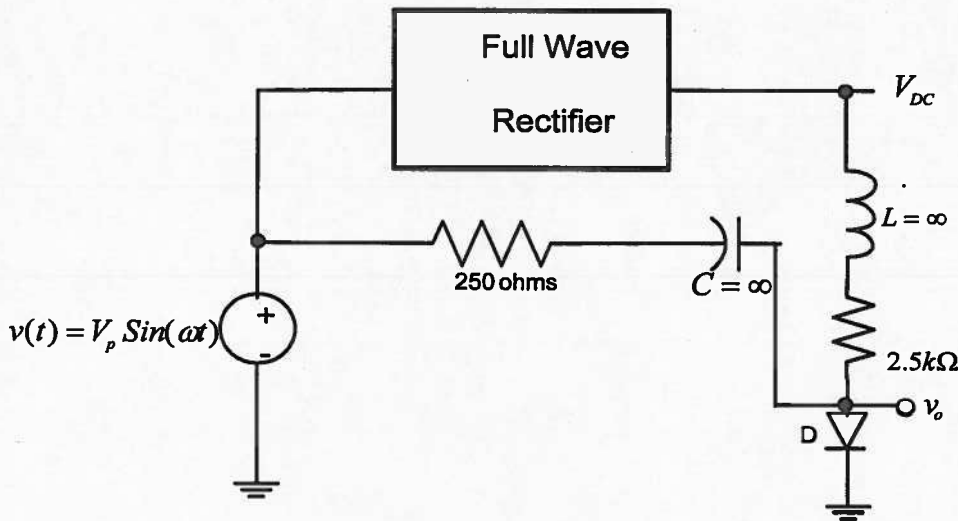


Figure 1:

You are required to find the amplitude of the ac output voltage v_o for a given amplitude V_p of the input signal. Please address the following questions.

- ac resistance
 $r_d = \left(\frac{I_{DQ}}{nV_T} \right)^{-1}$
 $i_D = I_S \exp \left(\frac{V_D}{nV_T} \right)$
 $\left. \frac{\partial i_D}{\partial v_D} \right|_{I_{DQ}} = \frac{1}{r_d} = \frac{I_{DQ}}{nV_T}$
- (a) How will you represent the diode to calculate the signal v_o ? (1.0 point: KB 3)
 (b) Show/derive the equivalent circuit model of the diode to do your work (3.0 points: PA1)
 (c) Show the overall equivalent circuit containing the diode for calculating v_o (4.0 points: PA2)
 (d) Find the value of the ac signal v_o (2.0 point: PA3)
- V_p need be given.
- (Total: 10 marks)

Part II: Answer any FIVE questions (Each question has 10 marks)

Q.2: An implanted bio-electronic device requires +3 and -3 volts for its operation. This is to be arranged by inductive coupling (i.e. a transformer) of a radio signal through the skin of the person. The magnitude of the radio signal is 1.5 volts at 1MHz.

- (a) Provide a schematic of the system which can deliver the required voltages of +3 and -3 volts. You can use transformer, diodes, capacitors and resistors. (Two voltage doubler systems will be needed. explain in words from text book)
- (b) Explain the operation of the circuit. If the capacitors used are 10pF ($pF=10^{-12}$ Farad) each, what value of resistors will be desirable for smooth DC voltages of +3 and -3 volts? $R_L \gg 500k\Omega$, assuming $\omega = 6.28 \times 10^6$ rad/s, $C_L \gg 5T$, $T=10^{-6}$ s

Q.3: The circuit in Fig.3 depicts a BJT configured as common collector amplifier. Find and use the ac parameter values of the transistor ($\beta=49$) to calculate the R_{in} , and R_{out} as shown on the schematic. Given $V_A=100$ Volts.

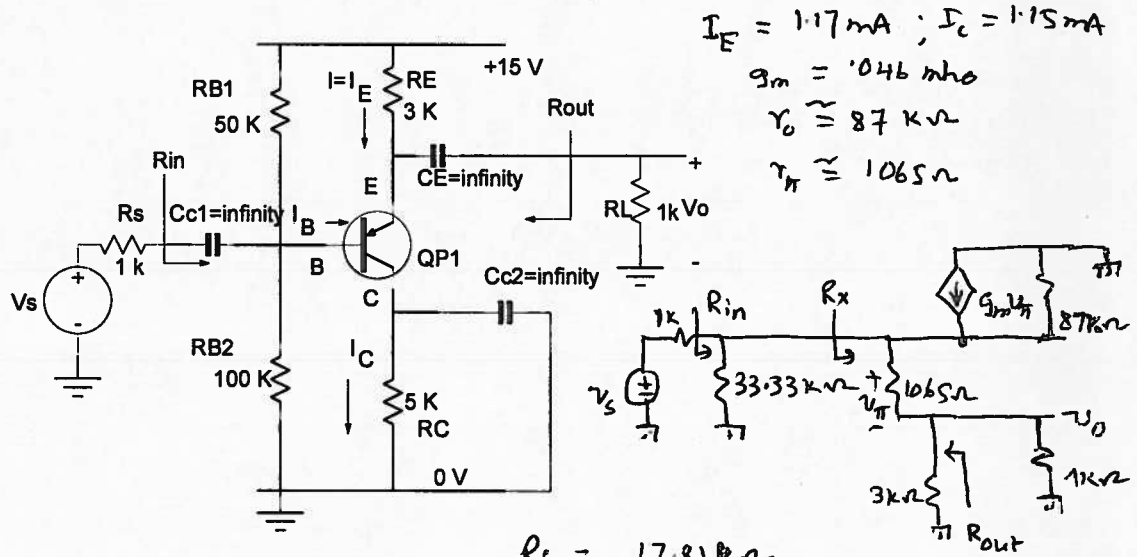
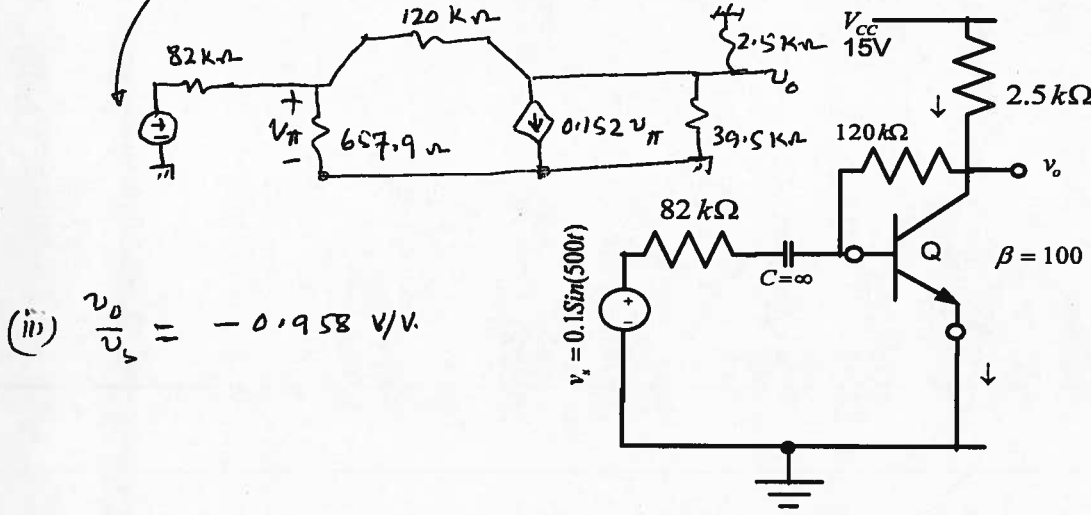


Figure 3:

Q.4: Figure 4 shows a BJT amplifier operating in *common emitter* configuration. The transistor has $\beta=100$, and V_A (i.e., *Early voltage*)=150 Volts. Find

- (i) The DC operating point $\rightarrow I_C = 3.8 \text{ mA}, V_o = 5.4 \text{ V}$
- (ii) The ac equivalent circuit $\rightarrow g_m = 0.152 \text{ mho}, r_{\pi} = 657.9 \Omega, r_o = 39.5 \text{ k}\Omega$
- (iii) The *small signal voltage gain* v_o/v_s .



(iii) $\frac{v_o}{v_s} = -0.958 \text{ V/V}$

Figure 4

Q.5: For a particular MOSFET operating in the saturation region at a constant v_{GS} , the i_D is found to be 0.5 mA for $v_{DS} = 1 \text{ V}$, and 0.52 mA at $v_{DS} = 2 \text{ V}$.

- (a) What are the values of r_o, V_A , and λ for this transistor? $r_o = 49.6 \text{ k}\Omega, V_A = 23.8 \text{ V}, \lambda = 0.042 \text{ V}^{-1}$
- (b) The transistors M1, M2 in Fig.5 have same r_o as in (a) above. For $I_D = 0.1 \text{ mA}, V_{DD} = 5 \text{ V}, V_{THN} = 0.7 \text{ V}, K_n = 100 \mu\text{A/V}^2$, and $W/L = 5$ for each transistor, what voltage gain v_o/v_{in} will be realized?

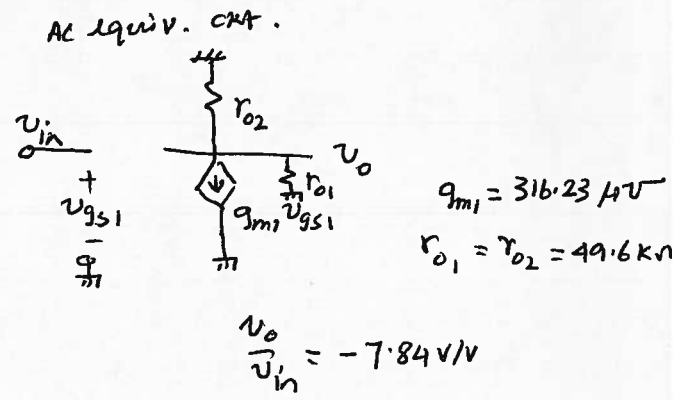
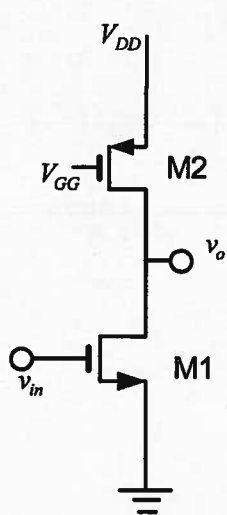


Figure 5:

Q.6: In the circuit of Fig. 6, the NMOS transistor has $|V_{TH}| = 0.6 \text{ V}$, $V_A = 75 \text{ V}$ and operates with $V_D = 1 \text{ V}$.

(a) What is the voltage gain v_o/v_i of this amplifier stage?

(b) What will V_D become if I is increased to $750 \mu\text{A}$?

$$\frac{v_o}{v_i} = -2.482 \text{ V/V}$$

$$V_D = 1.09 \text{ V}$$

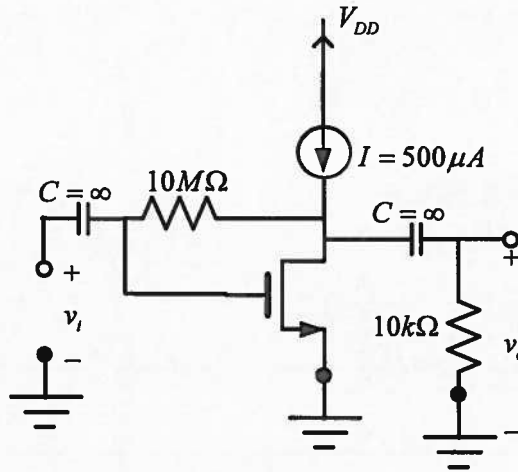


Figure 6:

Q.7: For the NMOS amplifier in Fig. 7, draw the *ac* equivalent circuit using T-model for the transistor, and assuming $r_o = \text{infinity}$. Derive expressions for the voltage gain v_s/v_i and v_d/v_i .

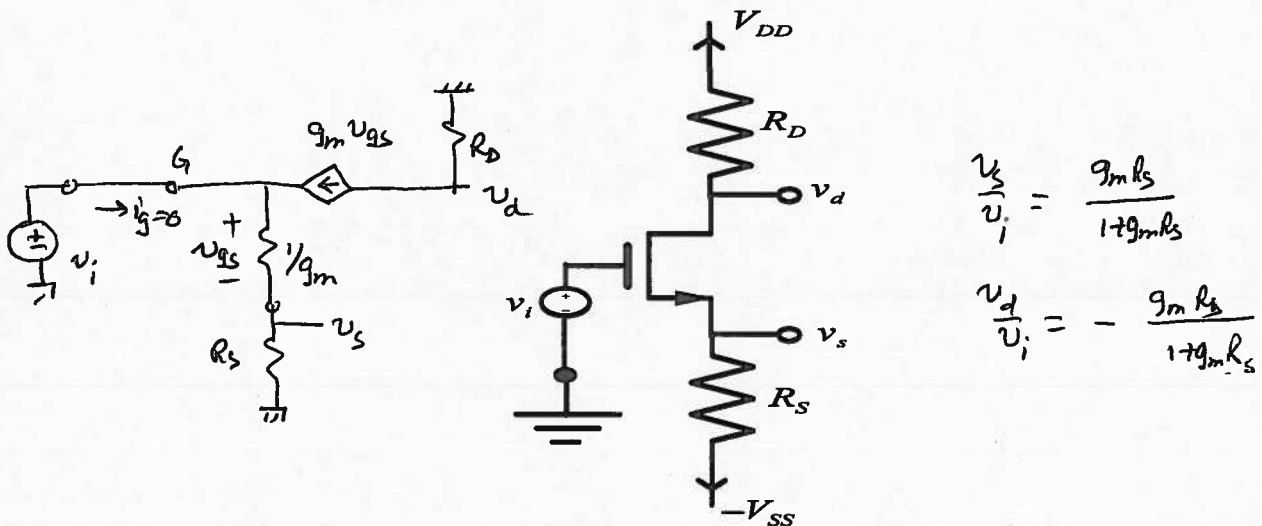


Figure 7: